What is claimed is:

1. A method for forming a pattern comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into at least two areas;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves; and

applying the resist filled in the grooves of the cliché onto the etching object layer by the divided area of the substrate.

2. The method of claim 1, wherein applying the resist on the etching object layer comprises:

providing a printing roll having a same width as that of the divided area of the substrate;

transferring the resist in the groove of the cliché onto a surface of the printing roll by contacting and rotating the printing roll on the cliché corresponding to the divided area of the substrate; and

applying the resist transferred on the surface of the printing roll on the etching object layer.

3. The method of claim 2, wherein a blanket is applied on the surface of the printing roll.

4. The method of claim 3, wherein a length of the blanket is the

same as a length of a circumference of the printing roll, which is same as a length of the divided area of the substrate.

5. The method of claim 1, wherein the divided area of the substrate includes one or more unit panels.

6. The method of claim 1, wherein the cliché is formed to have a same size as that of the divided area of the substrate.

7. The method of claim 1, wherein the printing roll is formed to have a same size as that of the divided area on the substrate.

8. The method of claim 1, wherein the etching object layer includes a metal layer.

9. The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiOx or SiNx.

10. The method of claim 1, wherein the etching object layer is a semiconductor layer.

11. A method for forming a pattern comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at

least one or more unit panels;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves of the cliché;

providing a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the groove of the cliché onto a surface of the printing roll by contacting and rotating the printing roll on the cliché; and

applying the resist transferred on the surface of the printing roll on the etching object layer.

12. The method of claim 11, wherein applying the resist on the etching object layer is performed by contacting the resist transferred on the surface of the printing roll on the substrate and by rotating the printing roll.

13. The method of claim 11, wherein the divided area of the substrate includes at least one unit panel.

14. The method of claim 11, wherein the etching object layer includes a metal layer.

15. The method of claim 11, wherein the etching object layer comprises an insulating layer comprised of SiOx or SiNx.

16. The method of claim 11, wherein the etching object layer is a semiconductor layer.

17. A pattern, which has been formed by:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into at least two areas;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves; and

applying the resist filled in the grooves of the cliché onto the etching object layer by the divided area of the substrate.

18. A pattern, which has been formed by:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at least one or more unit panels;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves of the cliché;

providing a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the groove of the cliché onto a surface of the printing roll by contacting and rotating the printing roll on the cliché; and

applying the resist transferred on the surface of the printing roll on the etching object layer.